



Bipolar NPN Bare Die – BTN909

Part Description

The BTN909 is a silicon BJT transistor available in bare die form and well suited for use in High Speed Switching applications.

Key Parameters:

- VCBO = 60V
- VCEO = 40V
- VEBO = 8V
- hFE = 100-300 @ VCE = 1V, IC = 0.15A
- VCE(Sat) = 0.4V @ IC = 0.15A, IB = 15mA
- fT = 250 MHz @ VCE = 10V, IE = 0A
- COBO = 6pF @ VCB = 5V

Features

Designed to provide performance equivalent to FAIRCHILD / ON SEMI MMBT4401, 2N4401

Die Size (Unawn)

370 μ m X 370 μ m, 15 Mils X 15 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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